TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7SG08AFS

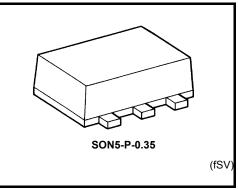
2 Input AND Gate

Features

- High-level output current: $I_{OH}/I_{OL} = \pm 8 \text{ mA (min)}$ at V_{CC} = 3.0 V
- High-speed operation: t_{pd} = 2.5 ns (typ.)

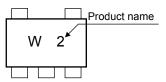
at V_{CC} = 3.3 V,15pF

- Operating voltage range: V_{CC} = 0.9~3.6 V
- 5.5-V tolerant inputs.

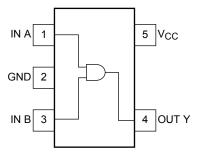


Weight: 0.001 g (typ.)

Marking



Pin Assignment (top view)



Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Value | Unit |
|------------------------------------|------------------|-----------------------------|------|
| Power supply voltage | V _{CC} | -0.5~4.6 | V |
| DC input voltage | VIN | -0.5~7.0 | V |
| DC output voltage | V _{OUT} | -0.5~ V _{CC} + 0.5 | V |
| Input diode current | I _{IK} | -20 | mA |
| Output diode current | I _{OK} | ±20 (Note 1) | mA |
| DC output current | IOUT | ±25 | mA |
| DC V _{CC} /ground current | ICC | ±50 | mA |
| Power dissipation | PD | 50 | mW |
| Storage temperature | T _{stg} | -65~150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Decemtions" (Operating Consent and Methoda) and individual reliability date (i.e. reliability text

("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: $V_{OUT} < GND, V_{OUT} > V_{CC}$

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Truth Table

| А | В | Y |
|---|---|---|
| L | L | L |
| L | Н | L |
| Н | L | L |
| Н | Н | Н |

IEC Logic Symbol



Operating Ranges

| Characteristics | Symbol | Value | Unit |
|--------------------------|----------------------------------|-------------------|------|
| Power supply voltage | V _{CC} | 0.9~3.6 | V |
| Input voltage | V _{IN} | 0~5.5 | V |
| Output voltage | V _{OUT} | 0~V _{CC} | V |
| Output Current | | ±8.0 (Note 2) | |
| | I _{OH} /I _{OL} | ±4.0 (Note 3) | |
| | | ±3.0 (Note 4) | mA |
| | | ±1.7 (Note 5) | ША |
| | | ±0.3 (Note 6) | |
| | | ±0.02 (Note 7) | |
| Operating temperature | T _{opr} | -40~85 | °C |
| Input rise and fall time | dt/dV | 0~10 (Note 8) | ns/V |

Note 2: V_{CC} = 3.0~3.6 V

Note 3: V_{CC} = 2.3~2.7 V

Note 4: $V_{CC} = 1.65 \sim 1.95 \text{ V}$

Note 5: $V_{CC} = 1.4 \sim 1.6 V$

Note 6: $V_{CC} = 1.1 \sim 1.3 V$

Note 7: $V_{CC} = 0.9 V$

Note 8: $V_{IN} = 0.8 \text{~} 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

DC Electrical Characteristics

| Characteristics | Symbol | nbol Test Condition | | Ta = 25°C | | | Ta = -40~85°C | | Unit | | |
|---|-----------------|-----------------------------------|--------------------------------|---------------------------|--|--|---------------------------|--|--|----|---|
| | | Condition | V _{CC} (V) | Min | Тур. | Max | Min | Max | Onit | | |
| High-level VIH input voltage | | | 0.9 | V _{CC} | | — | V _{CC} | _ | V | | |
| | | | | 1.1~1.3 | $\begin{array}{c} V_{CC} \\ \times \ 0.7 \end{array}$ | | _ | $\begin{array}{c} V_{CC} \\ \times \ 0.7 \end{array}$ | | — | |
| | VIH | | | 1.4~1.6 | V _{CC} × 0.65 | | — | V _{CC} × 0.65 | | _ | |
| | | | 1.65~1.95 | V _{CC} × 0.65 | | _ | V _{CC} × 0.65 | | | | |
| | | | | 2.3~2.7 | 1.7 | | _ | 1.7 | _ | | |
| | | | | 3.0~3.6 | 2.0 | | _ | 2.0 | _ | | |
| | | | | 0.9 | _ | _ | GND | — | GND | | |
| Low-level | | | | _ | _ | $V_{CC} \times 0.3$ | _ | $\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$ | V | | |
| | | | | | | $\begin{array}{c} V_{CC} \\ \times \ 0.35 \end{array}$ | _ | $\begin{array}{c} V_{CC} \\ \times \ 0.35 \end{array}$ | | | |
| input voltage | | | | 1.65~1.95 | | | V _{CC} × 0.35 | | V _{CC} × 0.35 | | |
| | | | 2.3~2.7 | _ | | 0.7 | | 0.7 | | | |
| | | | | 3.0~3.6 | _ | _ | 0.8 | | 0.8 | | |
| | | VIN = VIH | I _{OH} =-0.02 mA | 0.9 | 0.75 | _ | — | 0.75 | — | | |
| | | | I _{OH} = -0.3 mA | 1.1~1.3 | $\begin{array}{c} V_{CC} \\ \times \ 0.75 \end{array}$ | | _ | V _{CC} × 0.75 | _ | | |
| High-level | V _{ОН} | | VIN = VIH | I _{OH} = -1.7 mA | 1.4~1.6 | V _{CC} × 0.75 | _ | _ | V _{CC} × 0.75 | | V |
| output voltage | | | I _{OH} = -3.0 mA | 1.65~ 1.95 | V _{CC} -0.45 | _ | _ | V _{CC} -0.45 | _ | | |
| | | | I _{OH} = -4.0 mA | 2.3~2.7 | 2.0 | | _ | 2.0 | _ | | |
| | | | I _{OH} = -8.0 mA | 3.0~3.6 | 2.48 | | | 2.48 | _ | | |
| | | | I _{OL} = 0.02 mA | 0.9 | _ | | 0.1 | _ | 0.1 | V | |
| Low-level V _{OL} output voltage | | V _{IN} = V _{IH} | I _{OL} = 0.3 mA | 1.1~1.3 | | | V _{CC} × 0.25 | | V _{CC} × 0.25 | | |
| | Vol | | I _{OL} = 1.7 mA | 1.4~1.6 | | _ | V _{CC} × 0.25 | _ | $\begin{array}{c} V_{CC} \\ \times \ 0.25 \end{array}$ | | |
| | | or V _{IL} | IL I _{OL} = 3.0 mA | 1.65~ 1.95 | _ | _ | 0.45 | _ | 0.45 | | |
| | | | I _{OL} = 4.0 mA | 2.3~2.7 | _ | | 0.4 | _ | 0.4 | | |
| | | | I _{OL} = 8.0 mA | 3.0~3.6 | _ | _ | 0.4 | _ | 0.4 | | |
| Input leakage current | I _{IN} | V _{IN} = 0~5.5V | | 0~3.6 | _ | | ±0.1 | | ±1.0 | μA | |
| Quiescent supply current | Icc | $V_{IN} = V_{CC}$ or GND | | 3.6 | _ | | 1.0 | _ | 10.0 | μA | |

AC Electrical Characteristics (input $t_r = t_f = 3 \text{ ns}$)

| Characteristics | Symbol | Test Condition | | Ta = 25°C Ta = -40~85°C | | | 0~85°C | - Unit | |
|-------------------------------|-----------------|---|---------------------|-------------------------|------|------|--------|--------|------|
| | | | V _{CC} (V) | Min | Тур. | Max | Min | Max | Unit |
| | | $C_L = 10 \text{ pF},$ $R_L = 1 \text{ M}\Omega$ | 0.9 | | 26.9 | | _ | _ | |
| | | | 1.1~1.3 | | 10.9 | 18.4 | 1.0 | 34.2 | |
| | | | 1.4~1.6 | _ | 5.9 | 8.5 | 1.0 | 10.0 | |
| | | | 1.65~ 1.95 | _ | 4.5 | 6.2 | 1.0 | 6.7 | |
| | | | 2.3~2.7 | | 2.9 | 3.9 | 1.0 | 4.4 | |
| | | | 3.0~3.6 | | 2.2 | 3.1 | 1.0 | 3.7 | |
| | | | 0.9 | | 30.0 | | | | |
| | tрLH tpHL | C _L = 15 pF, R _L = 1 MΩ | 1.1~1.3 | | 12.0 | 21.5 | 1.0 | 37.2 | ns |
| Propagation delay time | | | 1.4~1.6 | _ | 6.5 | 9.3 | 1.0 | 11.2 | |
| | | | 1.65~ 1.95 | _ | 5.0 | 6.9 | 1.0 | 7.1 | |
| | | | 2.3~2.7 | _ | 3.2 | 4.4 | 1.0 | 5.0 | |
| | | | 3.0~3.6 | | 2.5 | 3.4 | 1.0 | 3.9 | |
| | | $C_L = 30 \text{ pF},$ $R_L = 1 \text{ M}\Omega$ | 0.9 | | 45.0 | | | | |
| | | | 1.1~1.3 | | 18.0 | 29.6 | 1.0 | 56.0 | |
| | | | 1.4~1.6 | _ | 8.9 | 13.1 | 1.0 | 15.9 | |
| | | | 1.65~ 1.95 | _ | 6.9 | 9.2 | 1.0 | 9.6 | |
| | | | 2.3~2.7 | | 4.4 | 5.7 | 1.0 | 6.1 | |
| | | | 3.0~3.6 | _ | 3.5 | 4.4 | 1.0 | 4.8 | |
| Input capacitance | C _{IN} | — | 3.6 | — | 3 | — | | — | pF |
| Power dissipation capacitance | C _{PD} | (Note9) | 0.9~3.6 | | 6 | _ | _ | _ | pF |

Note 9: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

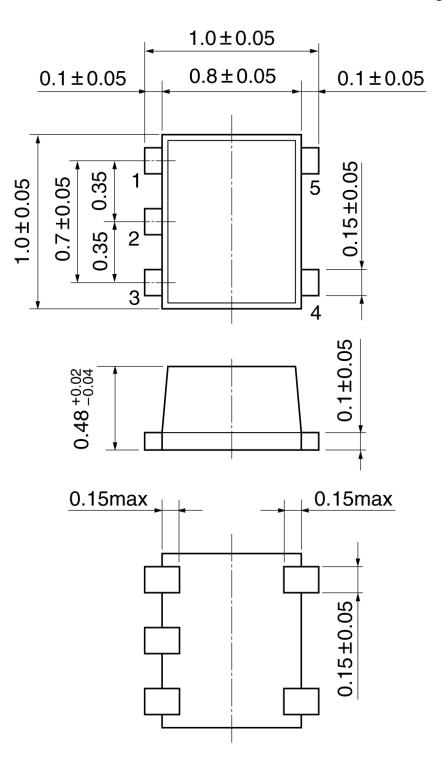
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

TOSHIBA

Package Dimensions

SON5-P-0.35

Unit:mm



Weight: 0.001 g (typ.)

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20070701-EN GENERAL

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